

Clean Copy of Claim 28

1 28. A method for forming a semiconductor device comprising at least a first
2 layer and a second layer with a component formed in the second layer, a first etch stop
3 layer being located between the first and second layers, and a second etch stop layer on
4 the second layer such that the second layer is located between the first and second etch
5 stop layers, the first etch stop layer being of depth greater than the second etch stop
6 layer, the method comprising the steps of:

A2 7 prior to forming the component in the second layer forming a communicating
8 bore through the first layer to the first etch stop layer adjacent a portion of the second
9 layer where the component is to be formed, and
10 10 etching a part of a portion of the first etch stop layer adjacent the portion of the
11 11 second layer where the component is to be formed for thinning the first etch stop layer
12 12 adjacent the portion of the second layer where the component is to be formed to an
13 13 effective stress relieving depth for relieving stress in the portion of the second layer
14 14 where the component is to be formed.